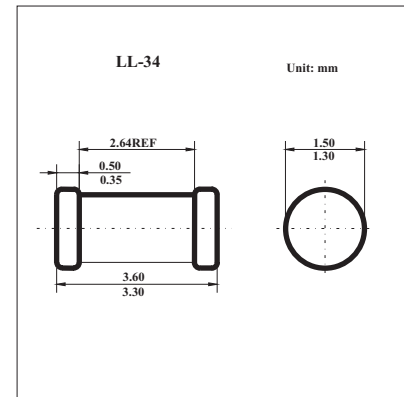


Schottky Barrier Diode

KAS85(BAS85)

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
continuous reverse voltage	V_R	30	V
continuous forward current	I_F	200	mA
average forward current ($V_{RWM} = 25\text{ V}$; $a = 1.57$; $\delta = 0.5$)	$I_{F(AV)}$	200	mA
repetitive peak forward current ($t_p \leq 1\text{ s}$; $\delta \leq 0.5$)	I_{FRM}	300	mA
non-repetitive peak forward current ($t_p = 10\text{ ms}$)	I_{FSM}	5	A
thermal resistance from junction to ambient	$R_{th\ j-a}$	320	K/W
operating ambient temperature	T_{amb}	-65 to +125	$^\circ\text{C}$
junction temperature	T_j	125	$^\circ\text{C}$
storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Max	Unit
forward voltage	V_F	$I_F = 0.1\text{ mA}$	240	mV
		$I_F = 1\text{ mA}$	320	
		$I_F = 10\text{ mA}$	400	
		$I_F = 30\text{ mA}$	500	
		$I_F = 100\text{ mA}$	800	
reverse current	I_R	$V_R = 25\text{ V}$ *	2.3	$\mu\text{ A}$
diode capacitance	C_d	$f = 1\text{ MHz}$; $V_R = 1\text{ V}$	10	pF

* Pulsed test: $t_p = 300\ \mu\text{s}$; $\delta = 0.02$.